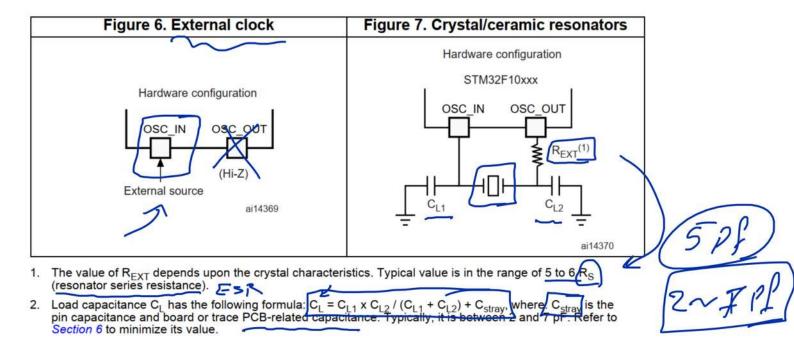


The high-speed external clock signal (HSE) can be generated from two clock sources:

- HSE external crystal/ceramic resonator (see Figure 7)
- HSE user external clock (see Figure 6)





External source (HSE bypass) 3.1.1

8 ~ 12 MHz

12 ~ 25 MHz

25 ~ 54 MHz

In this mode, an external clock source must be provided. It can have a frequency of up to:

60 Ω ~ 80 Ω

40 Ω ~ 60 Ω

30 Ω ~ 40 Ω

- 24 MHz for STM32F100xx value line devices
- 25 MHz for STM32F101xx, STM32F102xx and STM32F103xx devices
- 50 MHz for connectivity line devices

The external clock signal (square, sine or triangle) with a duty cycle of about 50%, has to drive the OSC_IN pin while the OSC_OUT pin must be left in the high impedance state (see Figure 7 and Figure 6).

3.1.2 External crystal/ceramic resonator (HSE crystal)

The external oscillator frequency ranges from:

4 to 16 MHz on STM32F101xx, STM32F102xx and STM32F103xx devices

4 to 24 MHz for STM32F100xx value line devices

3 to 25 MHz on connectivity line devices

The external oscillator has the advantage of producing a very accurate rate on the main clock. The associated hardware configuration is shown in Figure 7.

The resonator and the load capacitors have to be connected as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. The load capacitance values must be adjusted according to the selected oscillator.

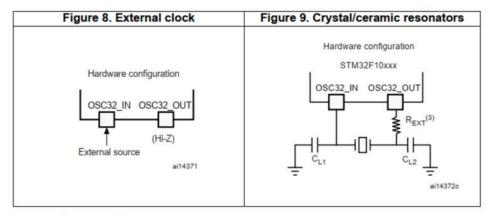
For C_{1,1} and C_{1,2} it is recommended to use high-quality ceramic capacitors in the 5 pF-to-25 pF range (typ.), designed for high-frequency applications and selected to meet the requirements of the crystal or resonator. CL1 and CL2 are usually the same value. The crystal manufacturer typically specifies a load capacitance that is the series combination of C_{I,1} and C_{I,2}. The PCB and MCU pin capacitances must be included when sizing C_{I,1} and C_{1.2} (10 pF can be used as a rough estimate of the combined pin and board capacitance).

Refer to the electrical characteristics sections in the datasheet for more details.

3.2 LSE OSC clock

The low-speed external clock signal (LSE) can be generated from two possible clock sources:

- LSE external crystal/ceramic resonator (see Figure 9)
- LSE user external clock (see Figure 8)



Note: 1 "External clock" figure:

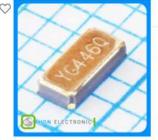
To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF), it is strongly recommended to use a resonator with a load capacitance $C_L \le 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.

2 "External clock" and "crystal/ceramic resonators" figures:

OSC32_IN and OSC_OUT pins can be used also as GPIO, but it is recommended not to use them as both RTC and GPIO pins in the same application.

3 "Crystal/ceramic resonators" figure:

The value of R_{EXT} depends on the crystal characteristics. A 0 Ω resistor works, but it is not optimal. Typical value is in the range of 5 to 6 R_S (resonator series resistance). To fine tune R_S value refer to AN2867 - Oscillator design guide for ST microcontrollers.



كريستال ساعت XKXGI-SUA-32.768K





1.Absolute maximum ratings					
Parameter(电气参数)	Symbol	Min. (最小值)	Typ.(典型值)	Max. (最大值)	Unit (单位)
Storage temperature (储存温度)	T_stg	-55	85.	125	°C
Maximum drive level (最大激励功率)	GL	-	0.1	-	μW

Parameter(电气参数)	Symbol	Min. (最小值)	Typ.(典型值)	Max. (最大值)	Unit (单位)
Type (型号)	YST310S				
Cutting Mode (切割方式)	⊠ x +2°				
Nominal frequency (标称频率)	f_nom	-	32.768	Y-	KHz
Frequency tolerance at 25℃ (常温频差)	f_tol	-20	-	20	x 10 ⁻⁶
Parabolic Coefficient(温飘系数)	В	-	12 L	- 0.04	x 10 ⁻⁶ / °C2
Load capacitance(负载电容)	CL	-	12.5	12	pF
Motional resistance (ESR) (等效谐振电阻)	R1	-		70	ΚΩ
Shunt capacitance (静电容)	C0	180	(: - /	1.4	pF
Motional capacitance (动态电容)	C1			3	fF
Operating temperature (工作温度)	T_use	-40	•	85	°C
Frequency aging (老化率)	f_age	-3	120	3	x10 ⁻⁶ /year

3.2.1 External source (LSE bypass)

In this mode, an external clock source must be provided. It can have a frequency up to 1 MHz. The external clock signal (square, sine or triangle) with a duty cycle of about 50% must drive the OSC32_IN pin, while the OSC32_OUT pin must be left high impedance (see *Figure 9* and *Figure 8*).

3.2.2 External crystal/ceramic resonator (LSE crystal)

The LSE crystal is a 32.768 kHz low-speed external crystal or ceramic resonator. It has the advantage of providing a low-power, but highly accurate clock source to the real-time clock peripheral (RTC) for clock/calendar or other timing functions.

The resonator and the load capacitors have to be connected as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. The load capacitance values must be adjusted according to the selected oscillator.

4.1 Boot mode selection

In the STM32F10xxx, three different boot modes can be selected by means of the BOOT[1:0] pins, as shown in *Table 2*.

BOOT mode selection pins				
BOOT1	воот0	Boot mode	Aliasing	
×	0	Main flash memory	Main flash memory is selected as boot space	
2	1	System memory	System memory is selected as boot space	
4	1	Embedded SRAM	Embedded SRAM is selected as boot space	

Table 2. Boot modes

The values on the BOOT pins are latched on the fourth rising edge of SYSCLK after a reset. It is up to the user to set the BOOT1 and BOOT0 pins after reset to select the required boot mode.

The BOOT pins are also resampled when exiting the Standby mode. Consequently, they must be kept in the required Boot mode configuration in the Standby mode. After this startup delay has elapsed, the CPU fetches the top-of-stack value from address 0x0000 0000, and starts code execution from the boot memory, starting from 0x0000 0004.

4.3 Embedded boot loader mode

The Embedded boot loader mode is used to reprogram the flash memory using one of the available serial interfaces:

- In low-density, low-density value line, medium-density, medium-density value line, and high-density devices, the boot loader is activated through the USART1 interface. For further details refer to AN2606.
- In XL-density devices, the boot loader is activated through the USART1 or USART2 (remapped) interface. For further details refer to AN2606.
- In connectivity line devices the boot loader can be activated through one of the
 following interfaces: USART1, USART2 (remapped), CAN2 (remapped) or USB OTG
 FS in Device mode (DFU: device firmware upgrade).
 The USART peripheral operates with the internal 8 MHz oscillator (HSI). The CAN and
 USB OTG FS, however, can only function if an external 8 MHz, 14.7456 MHz or
 25 MHz clock (HSE) is present. For further details, refer to AN2662.

This embedded boot loader is located in the System memory and is programmed by ST during production.

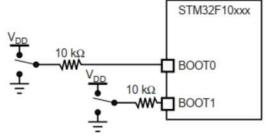


Figure 12. JTAG connector implementation

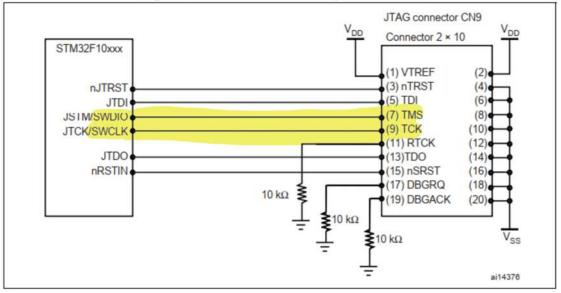


Table 5. Mandatory components

ld	Name	Reference	Quantity	Comments
1	Microcontroller	STM32F103ZE(T6)	1	144-pin package
2	Capacitors	100 nF	11	Ceramic capacitors (decoupling capacitors)
3	Capacitor	10 μF	1	Ceramic capacitor (decoupling capacitor)

Table 6. Optional components

1 Resistor 10 kΩ 5 Pull-up and pull-down for a Used for HSE: the value of characteristics. This resistor value is given example. 1 Resistor 1 Used for LSE: the value of characteristics. This resistor value is given example. 1 Used for LSE: the value of characteristics. This resistor value is given example. 2 Capacitor 1 Used for LSE: the value of characteristics. 3 Ceramic capacitor 4 Capacitor 1 Used for VDDA and VREF 6 Capacitor 10 pF 2 Used for LSE: the value of characteristics. 7 Capacitor 20 pF 2 Used for HSE: the value of characteristics. 8 Quartz 8 MHz 1 Used for HSE 9 Quartz 1 Used for LSE	ents
2 Resistor 390 Ω 1 characteristics. This resistor value is given example. 3 Resistor 0 Ω 1 Used for LSE: the value dicharacteristics. This resistor value is given example. 4 Capacitor 100 nF 3 Ceramic capacitor 5 Capacitor 1μF 2 Used for VDDA and VREF 6 Capacitor 10 pF 2 Used for LSE: the value dicharacteristics. 7 Capacitor 20 pF 2 Used for HSE: the value dicharacteristics. 8 Quartz 8 MHz 1 Used for HSE	JTAG and Boot mode.
3 Resistor 0 Ω 1 characteristics. This resistor value is given example. 4 Capacitor 100 nF 3 Ceramic capacitor 5 Capacitor 1µF 2 Used for VDDA and VREF 6 Capacitor 10 pF 2 Used for LSE: the value dicharacteristics. 7 Capacitor 20 pF 2 Used for HSE: the value dicharacteristics. 8 Quartz 8 MHz 1 Used for HSE	to Control of the Con
5 Capacitor 1μF 2 Used for VDDA and VREF 6 Capacitor 10 pF 2 Used for LSE: the value dicharacteristics. 7 Capacitor 20 pF 2 Used for HSE: the value dicharacteristics. 8 Quartz 8 MHz 1 Used for HSE	
6 Capacitor 10 pF 2 Used for LSE: the value dicharacteristics. 7 Capacitor 20 pF 2 Used for HSE: the value dicharacteristics. 8 Quartz 8 MHz 1 Used for HSE	
7 Capacitor 20 pF 2 characteristics. 7 Capacitor 20 pF 2 Used for HSE: the value of characteristics. 8 Quartz 8 MHz 1 Used for HSE	
7 Capacitor 20 pF 2 characteristics. 8 Quartz 8 MHz 1 Used for HSE	epends on the crystal
	epends on the crystal
9 Quartz 32 kHz 1 Used for LSE	
10 JTAG connector HE10 1 -	
11 Battery 3V3 1 If no external battery is use recommended to connect	
12 Switch 3V3 2 Used to select the correct	boot mode.
13 Push-button B1 1 -	

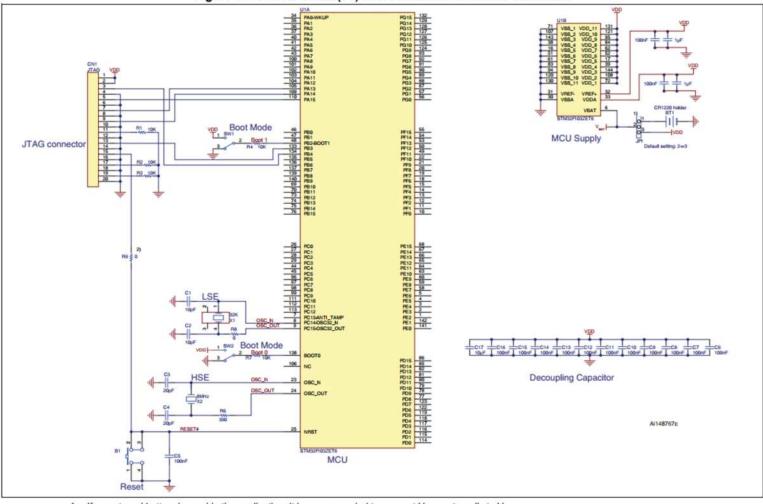
Via to V_{DD} V_{SS} Vall

V_{DD} V_{SS}

STM32F10xxx

Figure 13. Typical layout for V_{DD}/V_{SS} pair

Figure 14. STM32F103ZE(T6) microcontroller reference schematic



- 1. If no external battery is used in the application, it is recommended to connect VBAT externally to VDD-
- To be able to reset the device from the tools this resistor must be kept.